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FAIRCHILD

SEMICONDUCTOR

November 2013

FQI4N90

N-Channel QFET® MOSFET

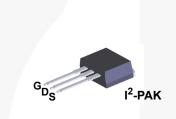
900 V, 4.2 A, 3.3 Ω

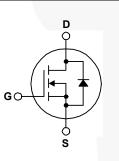
Description

This N-Channel enhancement mode power MOSFET is • 4.2 A, 900 V, $R_{DS(on)}$ = 3.3 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state D = 2.1 A Low Gate Charge (Typ. 24 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 9.5 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_{D} = 2.1 \text{ A}$





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

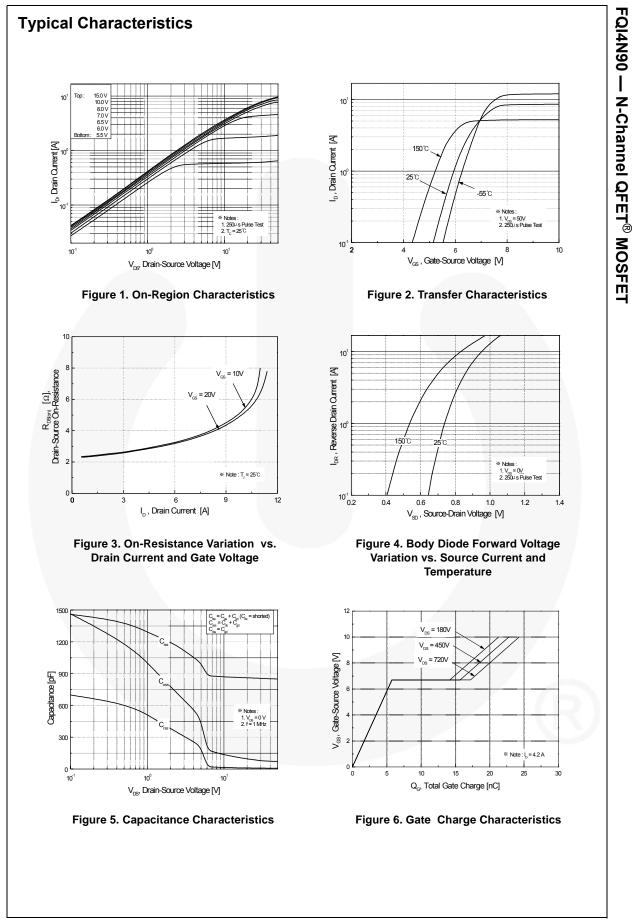
Symbol	Parameter	FQI4N90TU	Unit
V _{DSS}	Drain-Source Voltage	900	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)	4.2	А
	- Continuous (T _C = 100°C)	2.65	A
I _{DM}	Drain Current - Pulsed (No	ote 1) 16.8	A
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (No	ote 2) 570	mJ
I _{AR}	Avalanche Current (No	ote 1) 4.2	A
E _{AR}	Repetitive Avalanche Energy (No	ote 1) 14	mJ
dv/dt	Peak Diode Recovery dv/dt (No	ote 3) 4.0	V
PD	Power Dissipation (T _A = 25°C) *	3.13	W
	Power Dissipation ($T_C = 25^{\circ}C$)	140	W
	- Derate above 25°C	1.12	W/°C
T _J , T _{stg}	Operating and Storage Temperature Range	-55 to +150	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.	300	°C

Thermal Characteristics

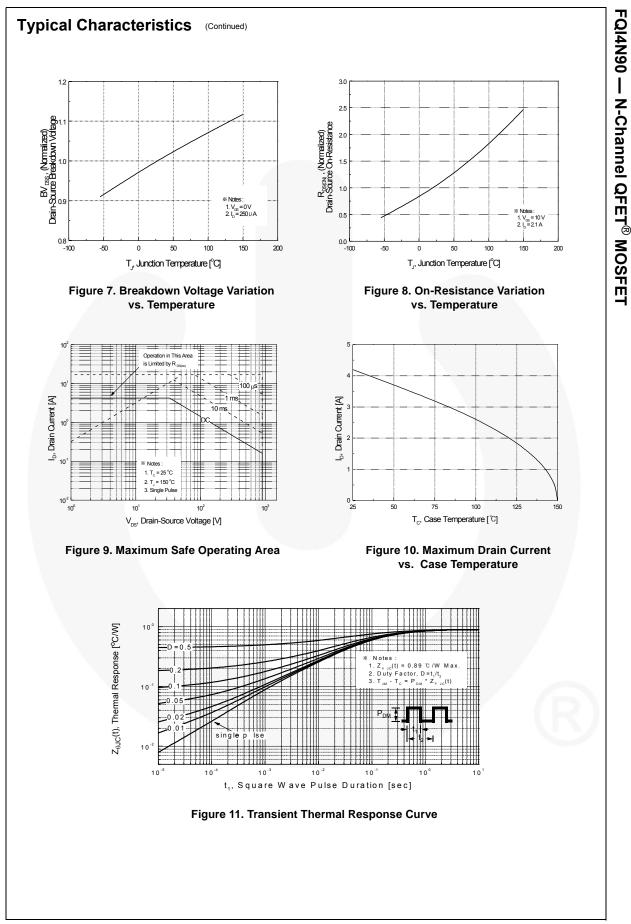
Symbol	Parameter	FQI4N90TU	Unit	
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	0.89		
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W	
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40		

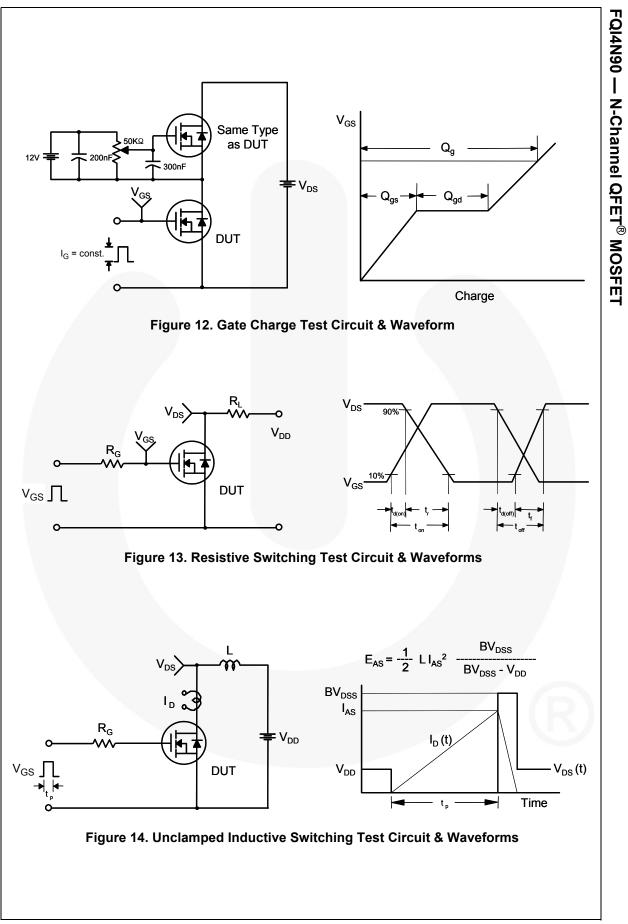
Faitin	lumber	mber Top Mark		Package Packing Metho		g Method	Reel Size		Tape Width		Quantity
FQI4N90TU		FQI4N90 I ²		PAK Tube N			N/	A	N/A		50 units
lectric	cal Cha	racteristics	T _C = 25°0	C unless oth	erwise noted						
Symbol	Parameter			Test Conditions				Min.	Тур.	Max	. Unit
		_									
	racterist										
BV _{DSS}	Drain-Source Breakdown Voltage		V _{GS} = 0 V, I _D = 250 μA			900			V		
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient			I_D = 250 μ A, Referenced to 25°C					0.9		V/°C
DSS	Zero Gate Voltage Drain Current			$V_{DS} = 900 V, V_{GS} = 0 V$ $V_{DS} = 720 V, T_{C} = 125^{\circ}C$					10	μA	
									100	μA	
GSSF	Gate-Bod	y Leakage Current,	Forward		V _{GS} = 30 V, V _{DS} = 0 V					100	nA
GSSR	Gate-Bod	y Leakage Current,	Reverse	V _{GS} =	-30 V, V _{DS}	; = 0 V				-100	nA
On Cha	racterist	ics									
V _{GS(th)}	Gate Thre	shold Voltage		V _{DS} = 7	V _{GS} , I _D =	250 μΑ		3.0		5.0	V
R _{DS(on)}	Static Dra On-Resist			V _{GS} =	10 V, I _D =	2.1 A			2.7	3.3	Ω
9 _{FS}	Forward T	ransconductance		V _{DS} =	50 V, I _D =	2.1 A			3.5		S
Dynami	ic Charad	cteristics									
C _{iss}	Input Cap	acitance	_	Vpc =	25 V, V _{GS}	= 0 V			860	1100	pF
C _{oss}	Output Ca	apacitance		f = 1.0		U I ,			90	120	pF
C _{rss}	Reverse 1	Transfer Capacitanc	e						9.5	12.5	pF
Switchi	ng Chara	acteristics									
t _{d(on)}		Delay Time	_	N/ -	450 \ ()	4.0.4			25	60	ns
t _r	Turn-On F	Rise Time		$R_{G} = 2$	450 V, I _D = 5 O	4.2 A,			70	150	ns
d(off)	Turn-Off D	Delay Time	-	$r_G - 2$	0 22				45	100	ns
lf	Turn-Off F	all Time				((Note 4)		40	90	ns
Qg	Total Gate	Charge		Vpc =	720 V, I _D =	= 4.2 A.			24	30	nC
ସୁ _{gs}	Gate-Sou	rce Charge		$V_{GS} =$	-	,			5.8		nC
Q _{gd}	Gate-Drai	n Charge		00	- 63		(Note 4)		11.5		nC
Drain-S	ource Di	ode Character	istics a	nd Max	imum F	Patings			1		
s	1	Continuous Drain-				-	- /			4.2	Α
с I _{SM}		Pulsed Drain-Sour								16.8	A
V _{SD}		Irce Diode Forward			0 V, I _S = 4	.2 A				1.4	V
t _{rr}		Recovery Time		$V_{GS} = 0 V, I_S = 4.2 A,$ $dI_F / dt = 100 A/\mu s$				440		ns	
		Recovery Charge						3.3		μC	

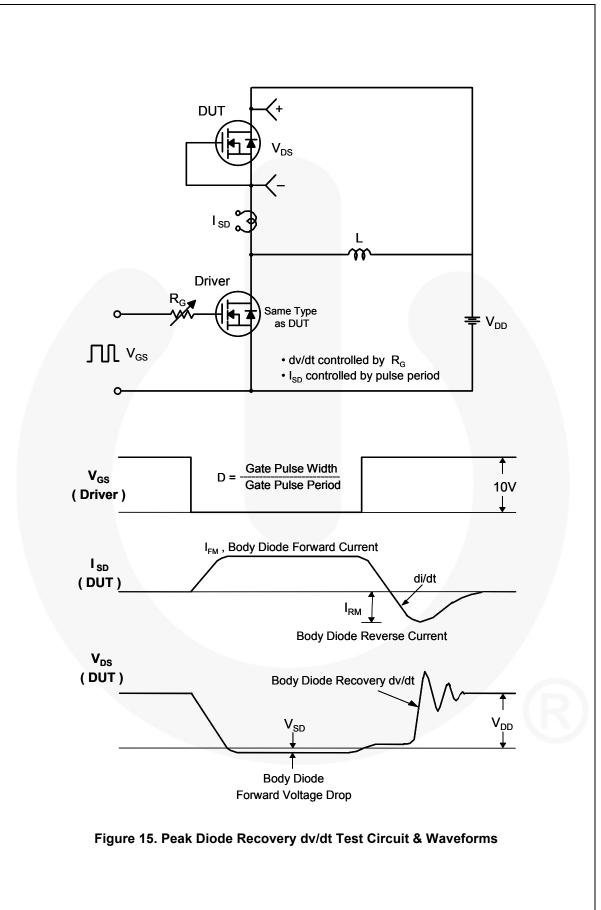
3. I_{SD} \leq 4.2 A, di/dt \leq 200 Å/µs, V_{DD} \leq BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature. FQI4N90 — N-Channel QFET[®] MOSFET

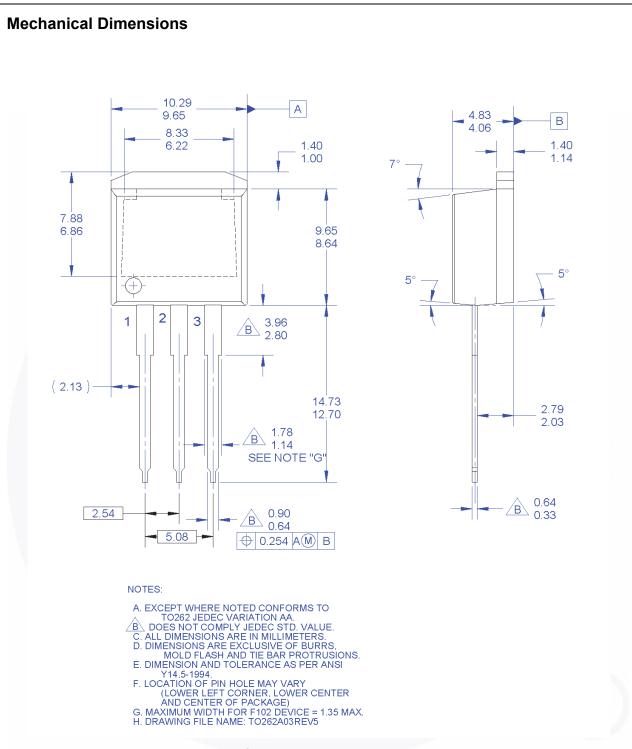


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FQI4N90 —

N-Channel QFET[®] MOSFET



QI4N90 —

Preliminary

No Identification Needed

Obsolete

First Production

Full Production

Not In Production

notice to improve design.

Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without

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